

TO-92MOD Plastic-Encapsulate Transistors

AV966 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM} : 0.9 \text{ W (Tamb=25)}$$

Collector current

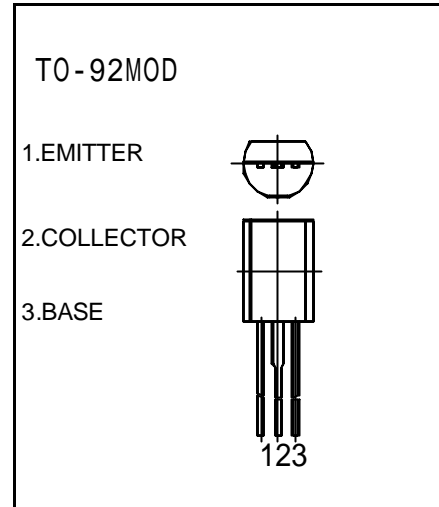
$$I_{CM} : -1.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -30 \text{ V}$$

Operating and storage junction temperature range

$$T_J , T_{stg} : -55 \text{ to } +150$$



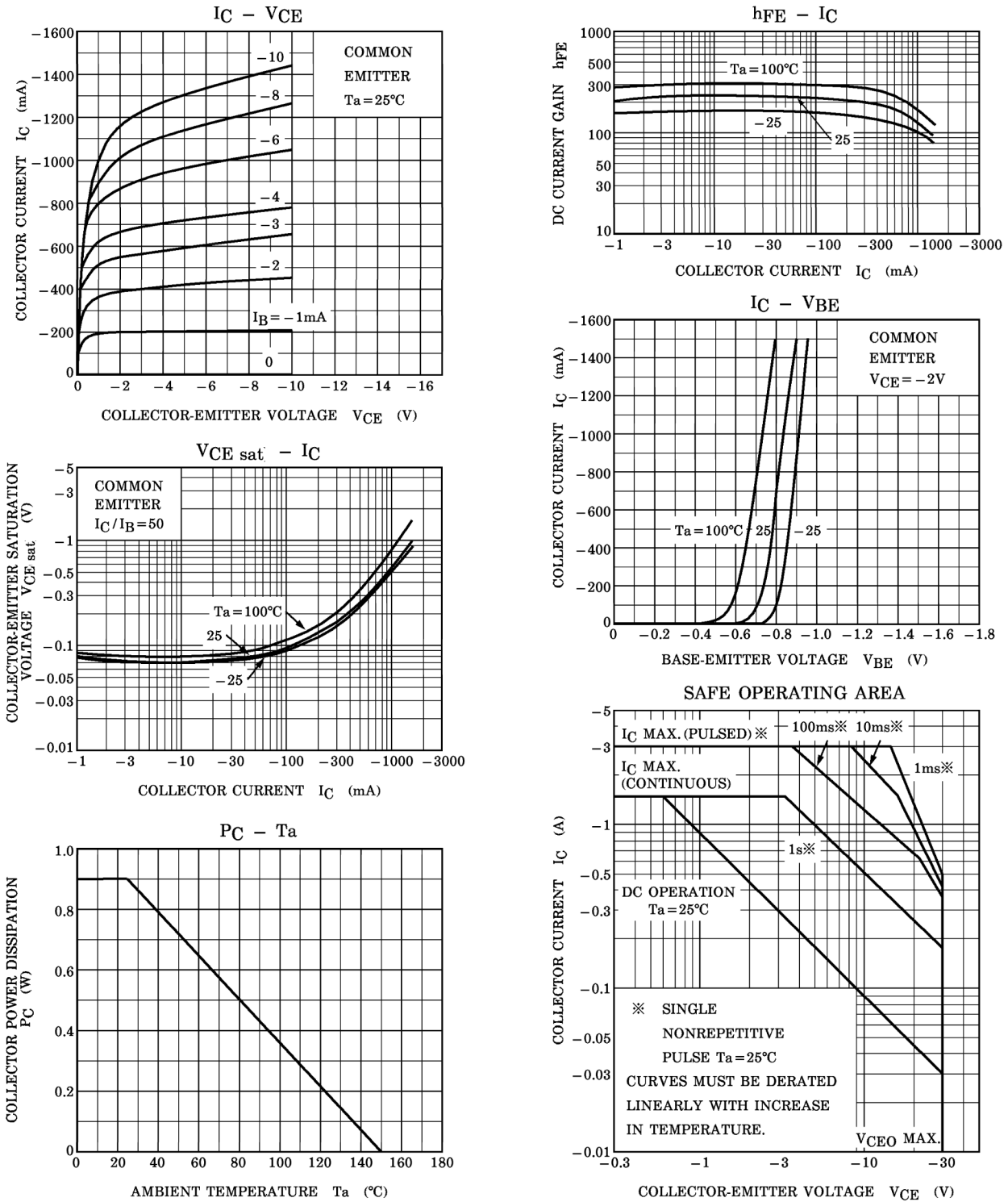
ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA} , I_E = 0$	-30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA} , I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA} , I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -30\text{V} , I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V} , I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2\text{V} , I_C = -500\text{mA}$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.5\text{A} , I_B = -0.03\text{A}$		-2	V
Base-emitter voltage	V_{BE}	$I_C = -500\text{mA} , V_{CE} = -2\text{V}$		-1	V
Transition frequency	f_T	$V_{CE} = -2\text{V} , I_C = -500\text{mA}$	100		MHz

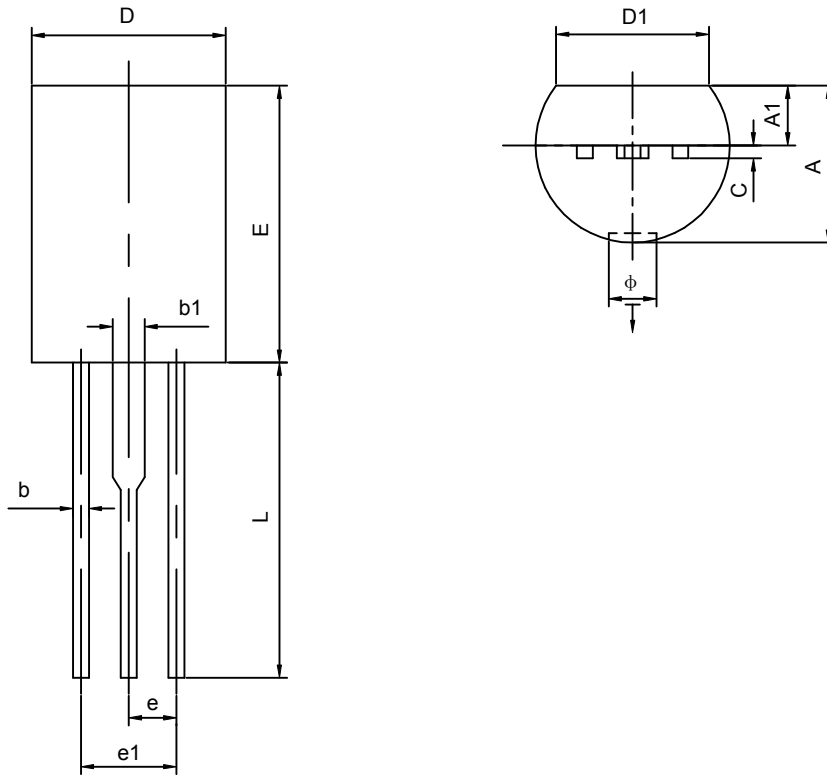
CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320

Typical Characteristics



TO-92MOD PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.700	5.100	0.185	0.201
A1	1.730	2.030	0.068	0.080
b	0.400	0.600	0.016	0.024
b1	0.900	1.100	0.035	0.043
c	0.400	0.500	0.016	0.020
D	5.800	6.200	0.228	0.244
D1	4.000		0.157	
E	8.400	8.800	0.331	0.346
e	1.500TYP		0.059TYP	
e1	2.900	3.100	0.114	0.122
L	13.050	13.450	0.514	0.530
Ö		1.600		0.063
∇	0.000	0.380	0.000	0.015